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Should be replaced with:

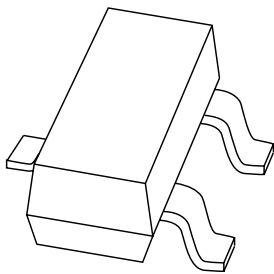
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via salesaddresses@nexperia.com). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



PMBT2369 NPN switching transistor

Product data sheet
Supersedes data of 1999 Apr 27

2004 Jan 22

NPN switching transistor

PMBT2369

FEATURES

- Low current (max. 200 mA)
- Low voltage (max. 15 V).

APPLICATIONS

- High-speed switching, especially in portable equipment.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.

MARKING

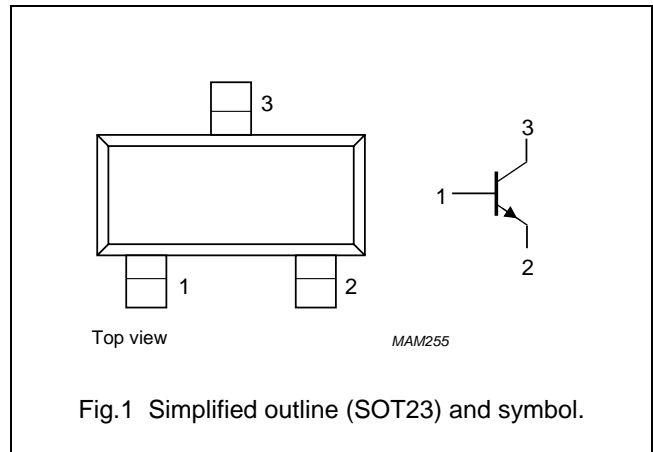
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBT2369	*1J

Note

- * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBT2369	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	40	V
V _{CEO}	collector-emitter voltage	open base	–	15	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	200	mA
I _{CM}	peak collector current		–	300	mA
I _{BM}	peak base current		–	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN switching transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

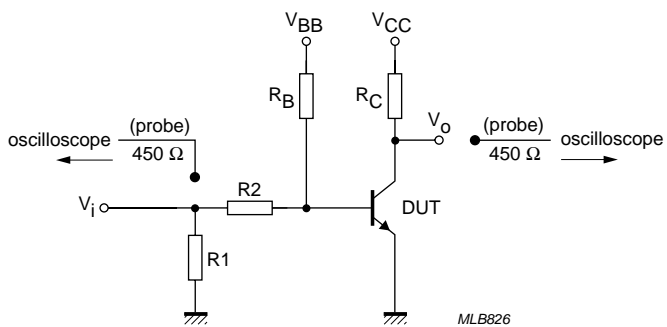
CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	400	nA
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 125\text{ °C}$	–	30	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	–	100	nA
h_{FE}	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 1\text{ V}$	40	120	
		$I_C = 10\text{ mA}; V_{CE} = 1\text{ V}; T_{amb} = -55\text{ °C}$	20	–	
		$I_C = 100\text{ mA}; V_{CE} = 2\text{ V}$	20	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	250	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	700	850	mV
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 5\text{ V}; f = 1\text{ MHz}$	–	4	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	500	–	MHz
Switching times (between 10% and 90% levels); (see Fig.2)					
t_{on}	turn-on time	$I_{Con} = 10\text{ mA}; I_{Bon} = 3\text{ mA};$ $I_{Boff} = -1.5\text{ mA}$	–	10	ns
t_d	delay time		–	4	ns
t_r	rise time		–	6	ns
t_{off}	turn-off time		–	20	ns
t_s	storage time		–	10	ns
t_f	fall time		–	10	ns

NPN switching transistor

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$V_i = 0.5$ to 4.2 V; $T = 500$ μ s; $t_p = 10$ μ s; $t_r = t_f \leq 3$ ns.
 $R_1 = 56$ Ω ; $R_2 = 1$ k Ω ; $R_B = 1$ k Ω ; $R_C = 270$ Ω .
 $V_{BB} = 0.2$ V; $V_{CC} = 2.7$ V.
 Oscilloscope input impedance $Z_i = 50$ Ω .

Fig.2 Test circuit for switching times.

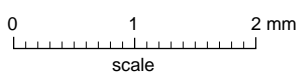
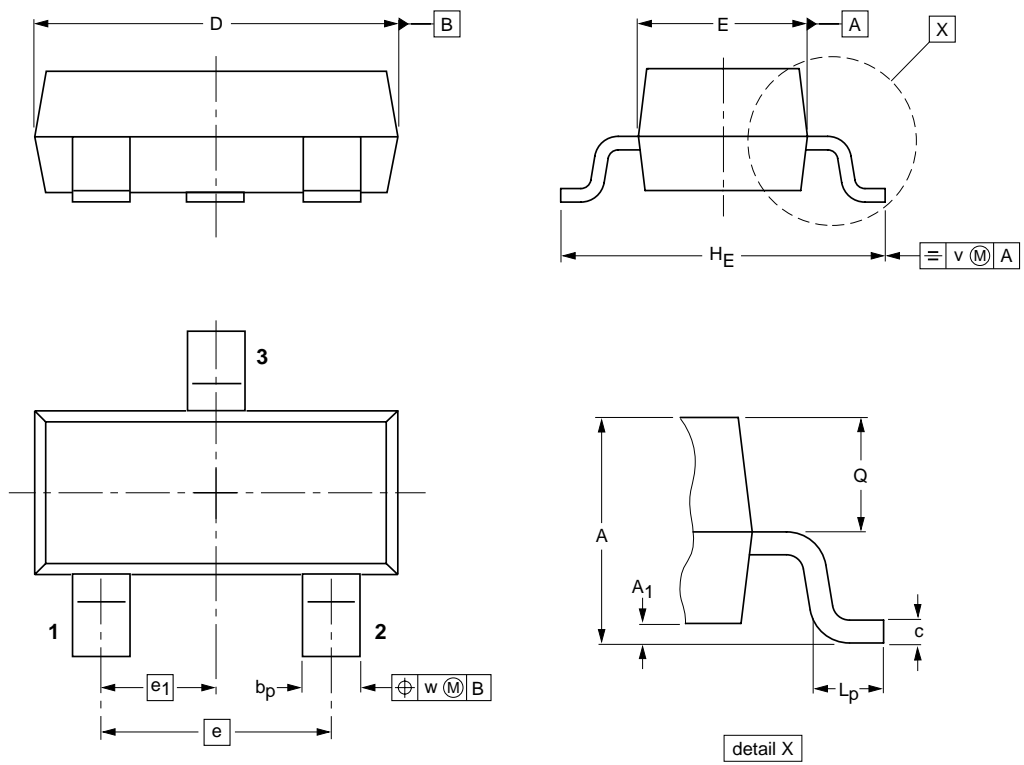
NPN switching transistor

PMBT2369

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16

NPN switching transistor

PMBT2369

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: <http://www.nxp.com>

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